5SNG 0300Q170300
62Pak phase leg IGBT Module

V_{CE} = 1700 V
I_C = 300 A

Ultra low-loss, rugged SPT++ chip-set
Smooth switching SPT++ chip-set for good EMC
Cu base-plate for low thermal resistance
Industry standard package
2 switches in one package

Maximum rated values [1)]

Parameter	Symbol	Conditions	min	max	Unit
Collector-emitter voltage	V_{CES}	V_{GE} = 0 V, T_{vj} ≥ 25 °C		1700	V
DC collector current	I_C	T_C = 100 °C, T_{vj} = 175 °C		300	A
Peak collector current	I_{CM}	t_p = 1 ms		600	A
Gate-emitter voltage	V_{GES}		-20	20	V
Total power dissipation	P_{tot}	T_C = 25 °C, T_{vj} = 175 °C, per switch		1875	W
DC forward current	I_F			300	A
Peak forward current	I_{FRM}	t_p = 1 ms		600	A
Surge current	I_{FSM}	V_R = 0 V, T_{vj} = 175 °C, t_p = 10 ms, half-sinewave		1800	A
IGBT short circuit SOA	t_{psc}	V_{CC} = 1300 V, $V_{CEM\ CHIP}$ ≤ 1700 V V_{GE} ≤ 15 V, T_{vj} ≤ 175 °C		10	μs
Isolation voltage	V_{isol}	1 min, f = 50 Hz		4000	V
Junction temperature	T_{vj}			175	°C
Junction operating temperature	$T_{vj(op)}$		-40	175	°C
Case temperature	T_C		-40	125 [2)]/150	°C
Storage temperature	T_{stg}		-40	125	°C
Mounting torques [3)]	M_s	Base-heatsink, M6 screws	3	6	Nm
	M_{t1}	Main terminals, M6 screws	3	6	Nm

[1)] Maximum rated values indicate limits beyond which damage to the device may occur per IEC 60747
[2)] for UL1557 compliance T_{Cmax} must be limited to 125°C
[3)] for detailed mounting instructions refer to ABB Document No. 5SYA 2106

IGBT characteristic values [4)]

Parameter	Symbol	Conditions		min	typ	max	Unit
Collector (-emitter) breakdown voltage	$V_{(BR)CES}$	V_{GE} = 0 V, I_C = 10 mA, T_{vj} = 25 °C		1700			V
Collector-emitter [5)] saturation voltage	$V_{CE\ sat}$	I_C = 300 A, V_{GE} = 15 V	T_{vj} = 25 °C		2.25	2.6	V
			T_{vj} = 125 °C		2.55		V
			T_{vj} = 175 °C		2.75		V
Collector cut-off current	I_{CES}	V_{CE} = 1700 V, V_{GE} = 0 V	T_{vj} = 25 °C			1	mA
			T_{vj} = 125 °C		1.5		mA
			T_{vj} = 175 °C		30		mA
Gate leakage current	I_{GES}	V_{CE} = 0 V, V_{GE} = ± 20 V, T_{vj} = 175 °C		-1		1	μA
Gate-emitter threshold voltage	$V_{GE(th)}$	I_C = 12 mA, V_{CE} = V_{GE}, T_{vj} = 25 °C		4.5		6.5	V
Gate charge	Q_G	I_C = 300 A, V_{CE} = 900 V, V_{GE} = -15 V ..15 V			2.1		μC
Input capacitance	C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz, T_{vj} = 25 °C			19.2		nF
Output capacitance	C_{oes}				1.7		nF
Reverse transfer capacitance	C_{res}				1.6		nF
Internal gate resistance	R_{Gint}	per switch			2.5		Ω
Turn-on delay time	$t_{d(on)}$	V_{CC} = 900 V, I_C = 300 A, R_G = 2.2 Ω, V_{GE} = ±15 V, $L_σ$ = 60 nH, inductive load	T_{vj} = 25 °C		260		ns
			T_{vj} = 125 °C		275		ns
			T_{vj} = 175 °C		285		ns
Rise time	t_r		T_{vj} = 25 °C		95		ns
			T_{vj} = 125 °C		98		ns
			T_{vj} = 175 °C		102		ns
Turn-off delay time	$t_{d(off)}$	V_{CC} = 900 V, I_C = 300 A, R_G = 2.2 Ω, V_{GE} = ±15 V, $L_σ$ = 60 nH, inductive load	T_{vj} = 25 °C		365		ns
			T_{vj} = 125 °C		455		ns
			T_{vj} = 175 °C		550		ns
Fall time	t_f		T_{vj} = 25 °C		160		ns
			T_{vj} = 125 °C		165		ns
			T_{vj} = 175 °C		180		ns
Turn-on switching energy	E_{on}	V_{CC} = 900 V, I_C = 300 A, R_G = 2.2 Ω, V_{GE} = ±15 V, $L_σ$ = 60 nH, inductive load	T_{vj} = 25 °C		75		mJ
			T_{vj} = 125 °C		95		mJ
			T_{vj} = 175 °C		115		mJ
Turn-off switching energy	E_{off}	V_{CC} = 900 V, I_C = 300 A, R_G = 2.2 Ω, V_{GE} = ±15 V, $L_σ$ = 60 nH, inductive load	T_{vj} = 25 °C		50		mJ
			T_{vj} = 125 °C		75		mJ
			T_{vj} = 175 °C		95		mJ
Short circuit current	I_{SC}	t_{psc} ≤ 10 μs, V_{GE} = 15 V, V_{CC} = 1300 V, $V_{CEM\ CHIP}$ ≤ 1700 V	T_{vj} = 175 °C		950		A

[4)] Characteristic values according to IEC 60747 – 9
[5)] Collector-emitter saturation voltage is given at chip level

Diode characteristic values [6)]

Parameter	Symbol	Conditions		min	typ	max	Unit
Forward voltage [7)]	V_F	I_F = 300 A	T_{vj} = 25 °C		1.6	2.2	V
			T_{vj} = 125 °C		1.75		V
			T_{vj} = 175 °C		1.7		V
Peak reverse recovery current	I_{RM}	V_{CC} = 900 V, I_F = 300 A, V_{GE} = ±15 V, R_G = 2.2 Ω, di/dt = 3.4 kA/µs, L_σ = 60 nH, inductive load	T_{vj} = 25 °C		330		A
			T_{vj} = 125 °C		390		A
			T_{vj} = 175 °C		450		A
Recovered charge	Q_r		T_{vj} = 25 °C		86		µC
			T_{vj} = 125 °C		131		µC
			T_{vj} = 175 °C		178		µC
Reverse recovery time	t_{rr}		T_{vj} = 25 °C		600		ns
			T_{vj} = 125 °C		720		ns
			T_{vj} = 175 °C		840		ns
Reverse recovery energy	E_{rec}		T_{vj} = 25 °C		50		mJ
			T_{vj} = 125 °C		75		mJ
			T_{vj} = 175 °C		110		mJ

[6)] Characteristic values according to IEC 60747 – 2
[7)] Forward voltage is given at chip level

Package properties [8)]

Parameter	Symbol	Conditions		min	typ	max	Unit
IGBT thermal resistance junction to case	$R_{th(j-c)IGBT}$	per switch				0.080	K/W
Diode thermal resistance junction to case	$R_{th(j-c)DIODE}$					0.120	K/W
IGBT thermal resistance [3)] case to heatsink	$R_{th(c-s)IGBT}$	IGBT per switch, λ grease = 1W/m x K			0.033		K/W
Diode thermal resistance [3)] case to heatsink	$R_{th(c-s)DIODE}$	Diode per switch, λ grease = 1W/m x K			0.050		K/W
Comparative tracking index	CTI			200			
Module stray inductance	$L_{\sigma\ CE}$	per switch			20		nH
Resistance, terminal-chip	$R_{CC'+EE'}$	per switch	T_C = 25 °C		0.7		mΩ
			T_C = 125 °C		0.98		
			T_C = 175 °C		1.12		

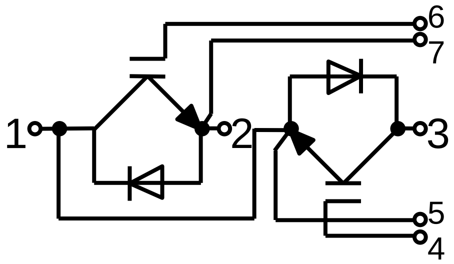
[3)] For detailed mounting instructions refer to ABB Document No. 5SYA 2106

Mechanical properties [8)]

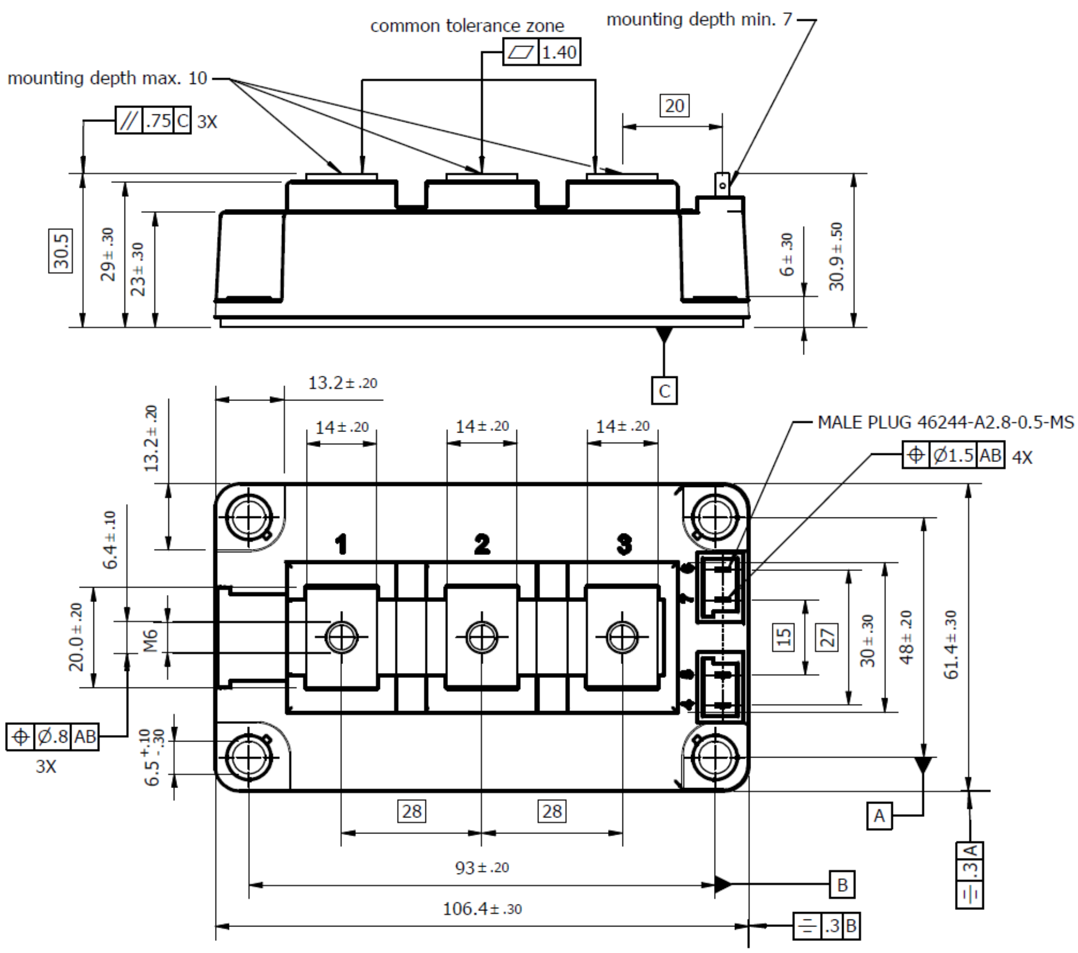
Parameter	Symbol	Conditions		min	typ	max	Unit
Dimensions	L x W x H	Typical			106.4 x 61.4 x 30.9		mm
Clearance distance in air	d_a	according to IEC 60664-1 and EN 50124-1	Term. to base:	23			mm
			Term. to term:	11			
Surface creepage distance	d_s	according to IEC 60664-1 and EN 50124-1	Term. to base:	29			mm
			Term. to term:	23			
Mass	m				330		g

[8)] Package and mechanical properties according to IEC 60747 – 15

Electrical configuration



Outline drawing [3)]



Note: all dimensions are shown in millimeters
[3)] For detailed mounting instructions refer to ABB Document No. 5SYA 2106

This is an electrostatic sensitive device, please observe the international standard IEC 60747-1, chap. VIII.
This product has been designed and qualified for Industrial Level.

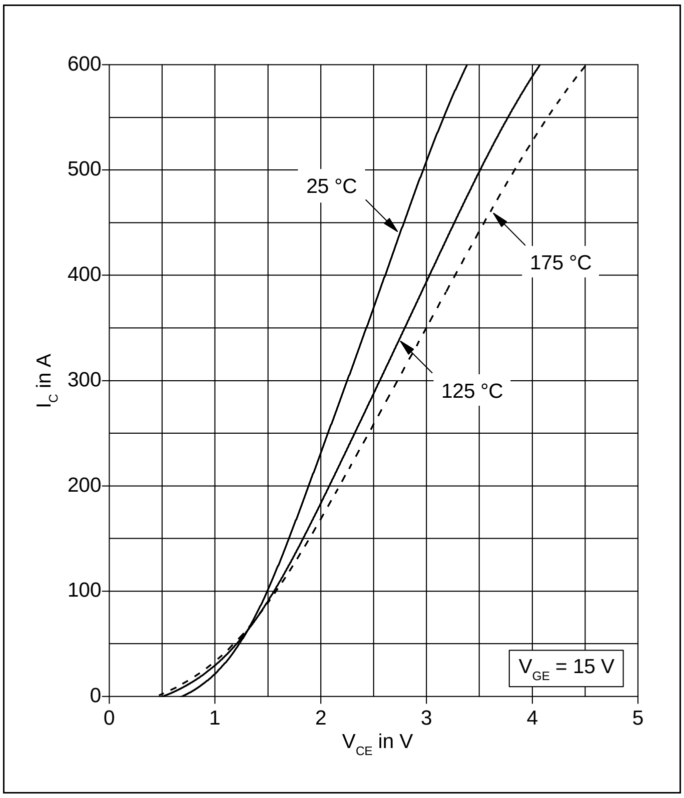


Fig. 1 Typical on-state characteristics, chip level

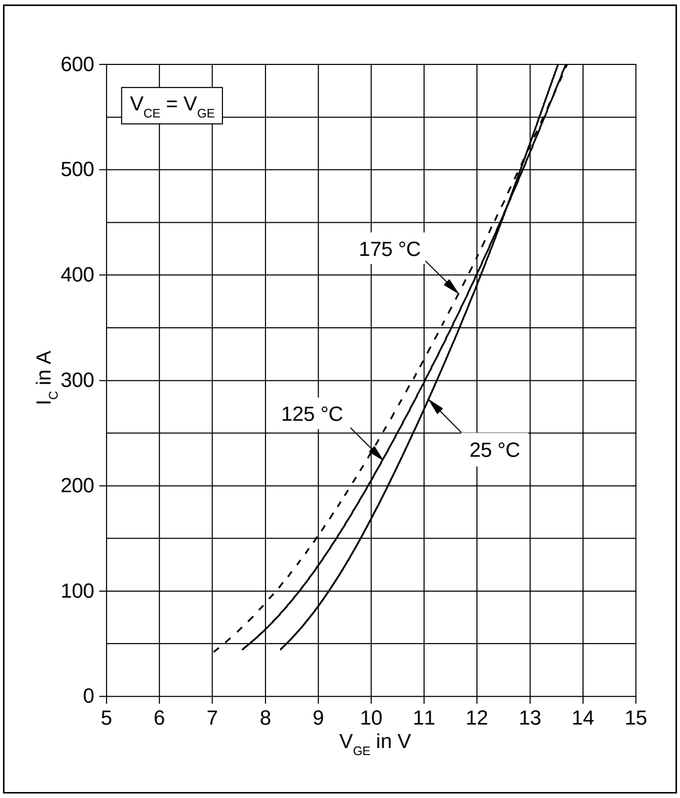


Fig. 2 Typical transfer characteristics, chip level

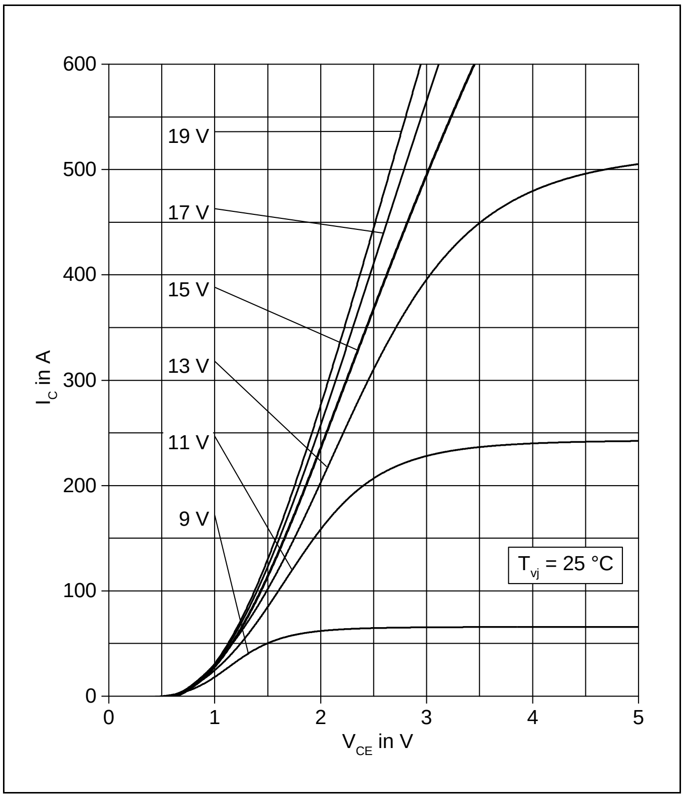


Fig. 3 Typical output characteristics, chip level

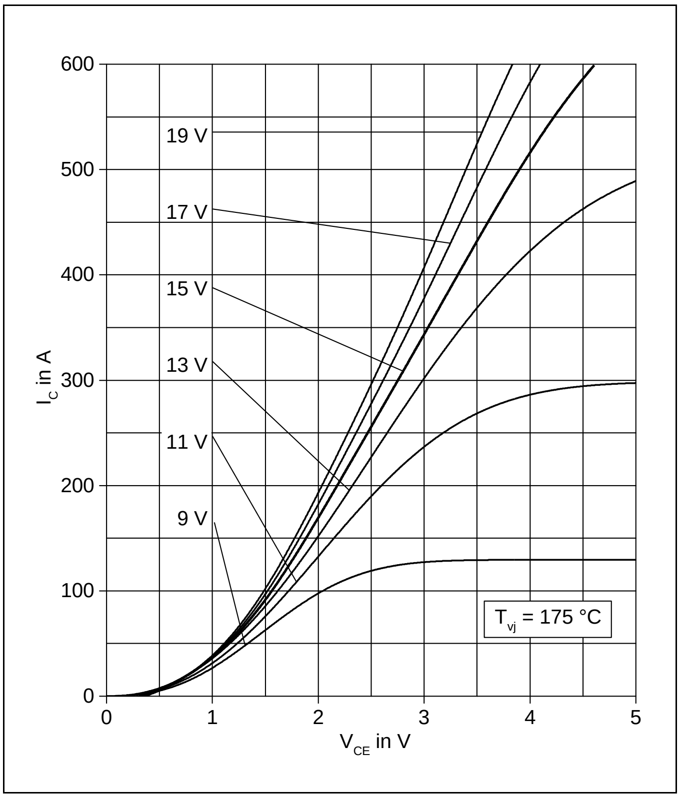


Fig. 4 Typical output characteristics, chip level

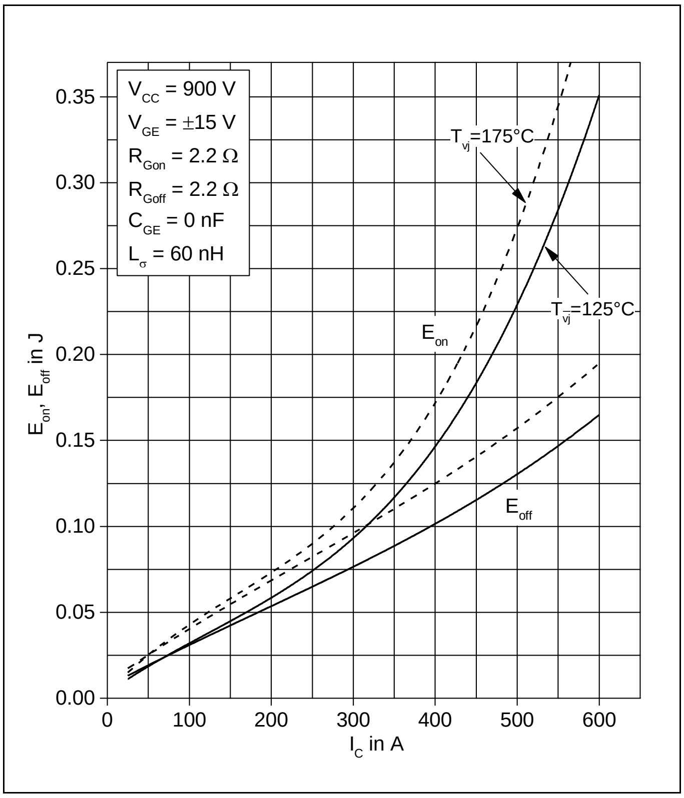


Fig. 5 Typical switching energies per pulse vs. collector current

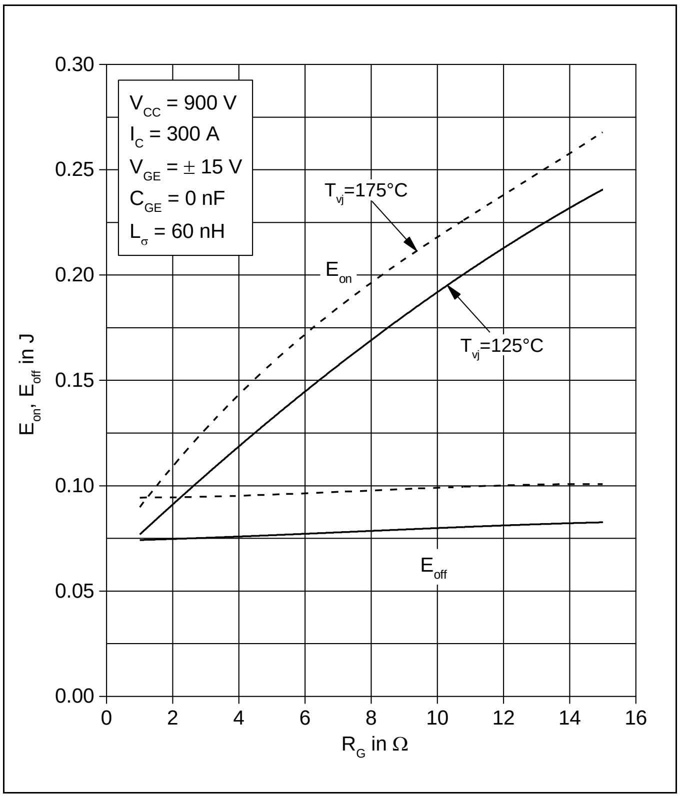


Fig. 6 Typical switching energies per pulse vs. gate resistor

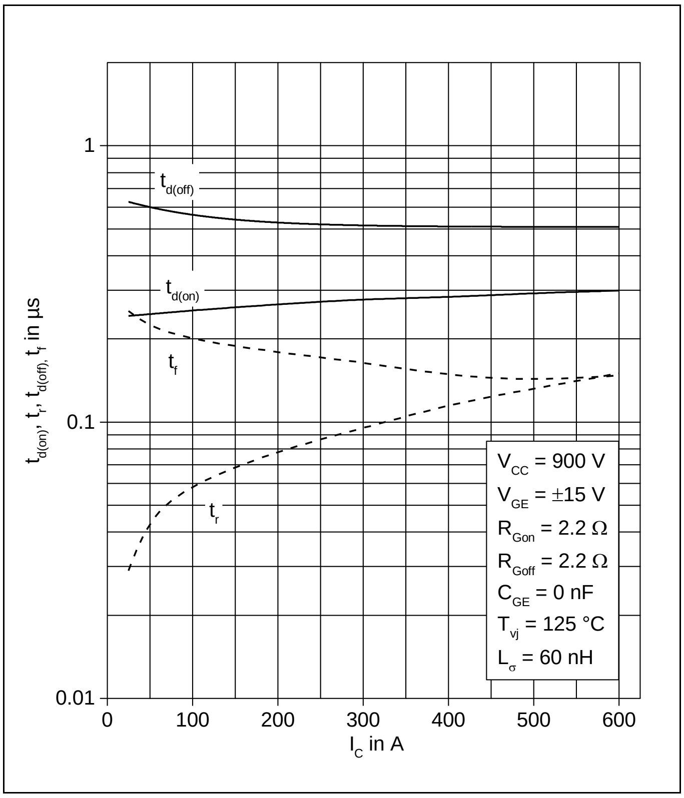


Fig. 7 Typical switching times vs. collector current

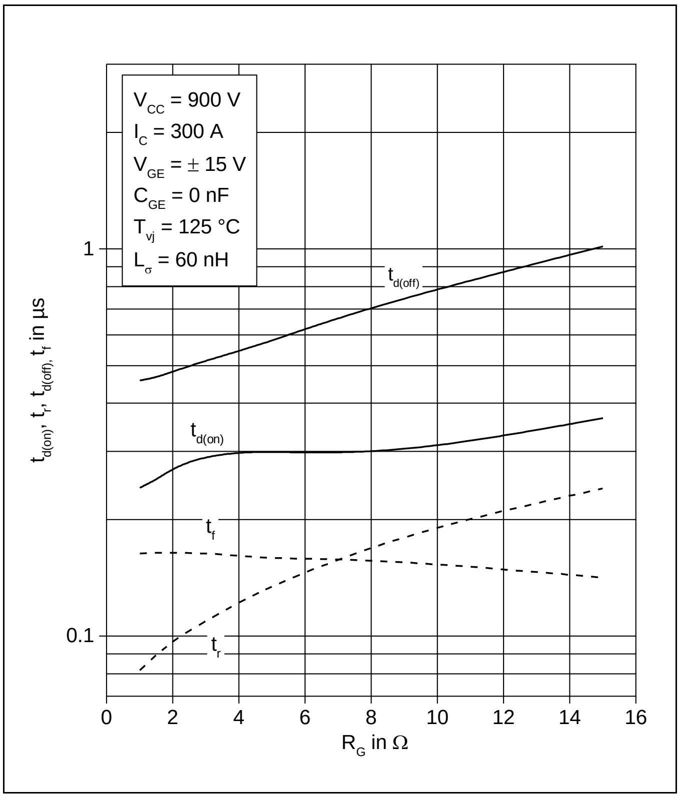


Fig. 8 Typical switching times vs. gate resistor

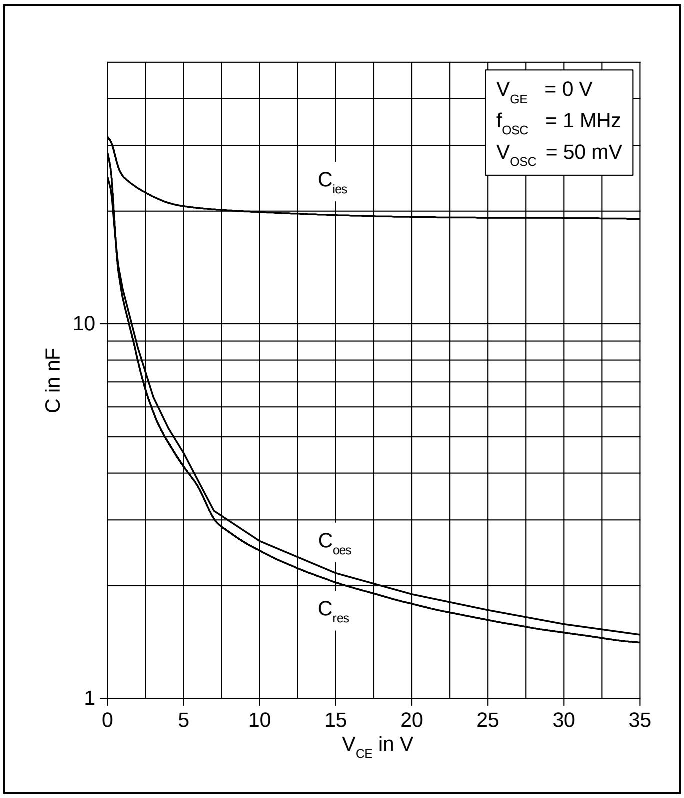


Fig. 9 Typical capacitances vs. collector-emitter voltage

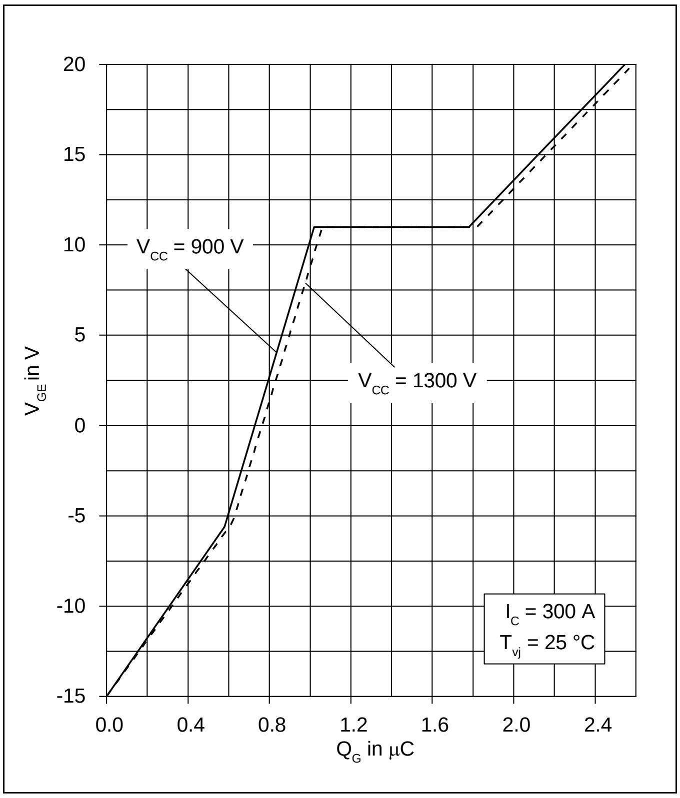


Fig. 10 Typical gate charge characteristics

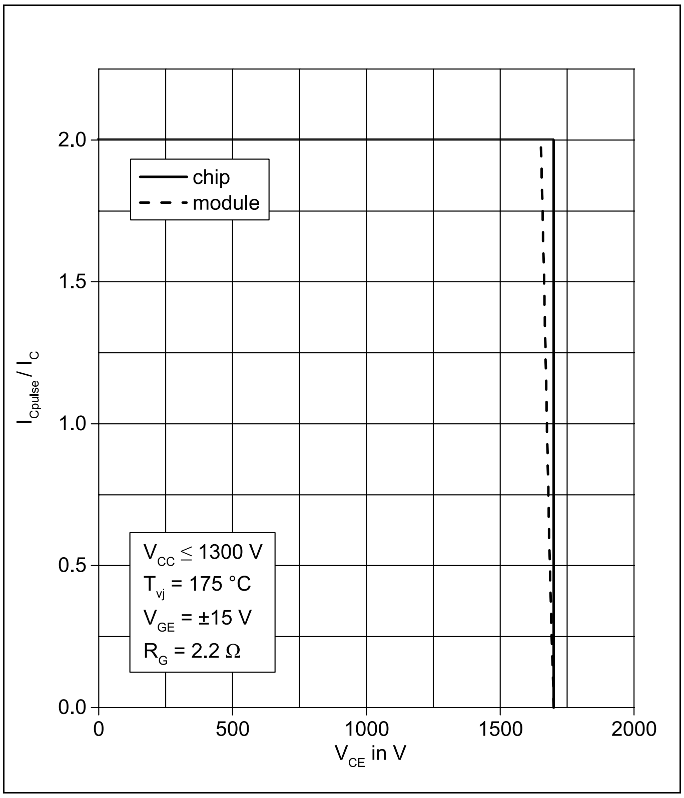


Fig. 11 Turn-off safe operating area (RBSOA)

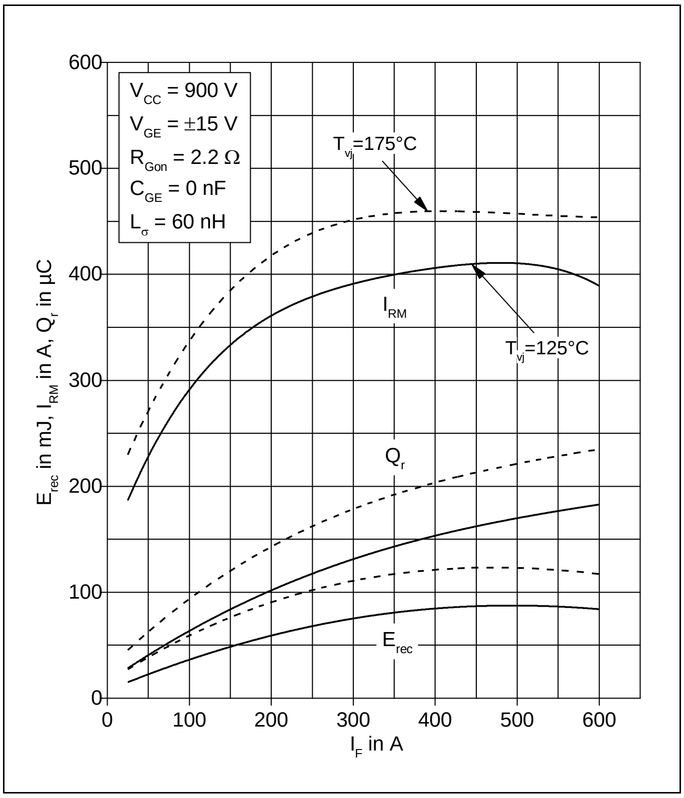


Fig. 12 Typical reverse recovery characteristics vs. forward current

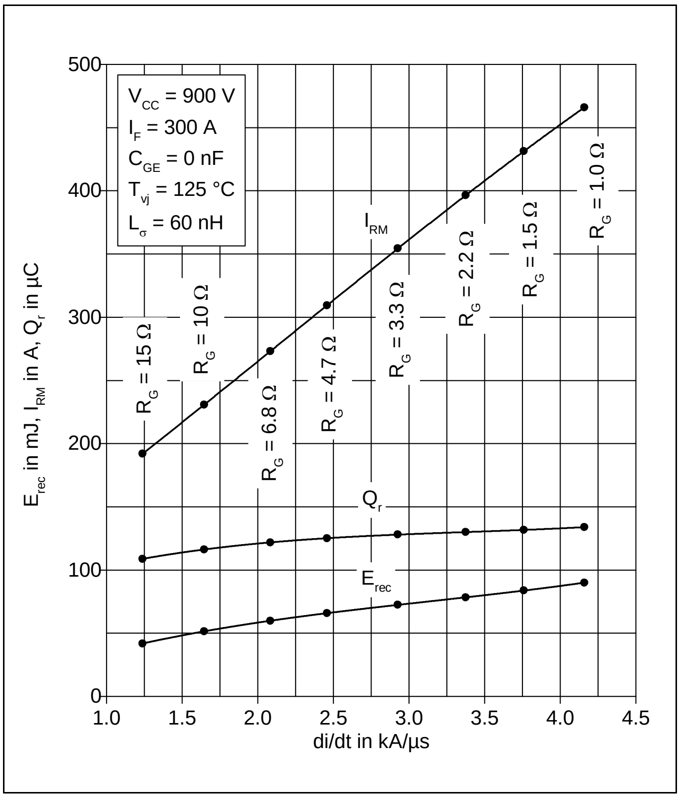


Fig. 13 Typical reverse recovery characteristics vs. di/dt

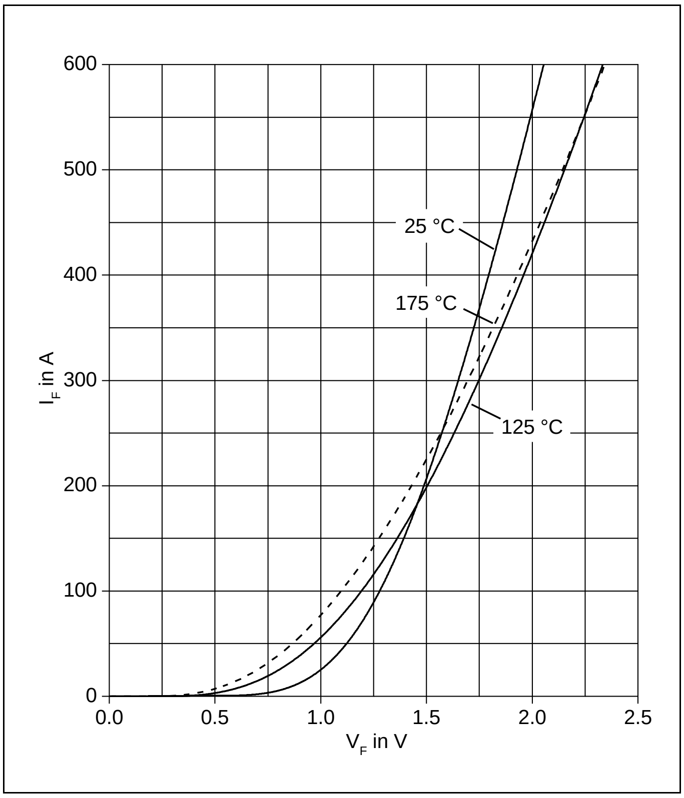


Fig. 14 Typical diode forward characteristics, chip level

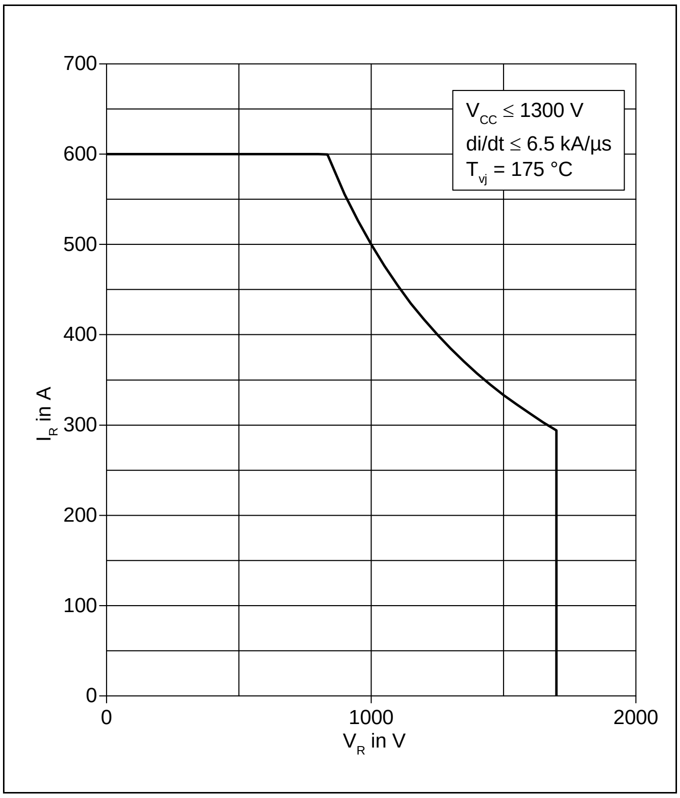


Fig. 15 Safe operating area diode (SOA)

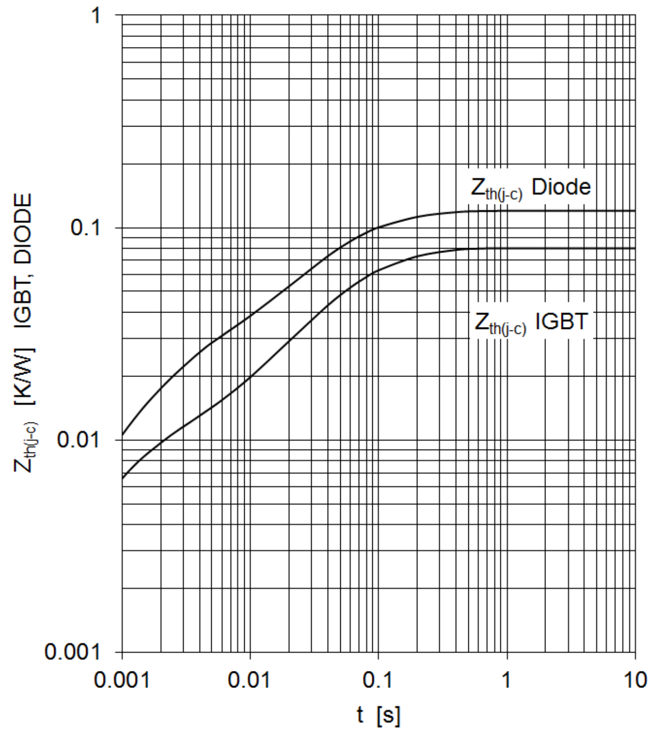


Fig. 16 Thermal impendance vs. time

Analytical function for transient thermal impedance:

$$Z_{th\,(j\text{-}c)}(t) = \sum_{i=1}^{n} R_i \left(1 - e^{-t/\tau_i}\right)$$

	i	1	2	3	4	5
IGBT	R_i(K/kW)	8.1	44.2	27.7		
	τ_i(ms)	0.9	40.2	136		
DIODE	R_i(K/kW)	20.2	30.9	68.9		
	τ_i(ms)	1.8	137	37.2		

Related documents:

5SYA 2042 Failure rates of IGBT modules due to cosmic rays
5SYA 2045 Thermal runaway during blocking
5SYA 2053 Applying IGBT
5SYA 2058 Surge currents for IGBT diodes
5SYA 2093 Thermal design and temperature ratings of IGBT modules
5SYA 2098 Paralleling of IGBT modules

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